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U.S. PATENT OR PUBLISHED U.S. PATENT APPLICATION DOCUMENTS

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	WO9534504	12/21/95	PCT			

OTHER DOCUMENTS (Including Author, Title, Date, Place of publication)

		Kim, Hyun-Tak et al, "Gate Induced Mott Transition", 5/27/03, <i>New Journal of Physics</i>
		Malinenko, V.P., "Metal-Semiconductor Phase Transition in Structurally Disordered Vanadium Dioxide". 5/3/83, <i>American Institute of Physics</i>
		Zhang, J.G et al, "The Switching Mechanism in V2O5 Gel Films", 3/14/88, <i>Journal of Applied Physics</i>
		Stefanovich, G. et al, "Electrical Switching and Mott Transition in VO2", 7/24/2000, <i>Journal of Physics</i>
		Boriskov, P.P et al, "The Effect of Electric Field on Metal-Insulator Phase Transition in Vanadium Dioxide", 12/28/01, <i>American Institute of Physics</i>
Examiner	/Long Pham/ (11/12/2007)	
	DATE CONSIDERED	
Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

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